



6ULC1R6V5

Ultra-Low Capacitance TVS

Features

- Ultra Low Capacitance 0.5pF
- High ESD Protection Level IEC61000-4-2 +/-8kV(Contact)
- Stand-off Voltage:5V
- For Small Package DFN0603,SOD-923

Applications

- Cell Phone
- PDA
- Other Electronics Equipments

Item	Characteristics
Wafer size	6inch
Chip size	235 * 235 um
Top metalization	Al-Si-Cu

Maximum Ratings (Ta=25degC)(*1)

Symbol	Parameter	Value	Units
T _{stg}	Storage temperature Range	-55 to+150	Deg C
T _j	Maximum junction temperature	-55 to+125	Deg C
I _{pp}	Peak pulse current(t=8/20usec)	3	A
V _{pp}	Electrostatic discharge IEC61000-4-2 Contact Discharge Air Discharge (*2)	+/-8 +/-15	kV kV

(*1) All Rating values for reference on a SOT-23 package configuration (front: Au wire 35um, back: Au eutectic),
mounted on PCB of 1.5cm by 2.5cm.

(*2) Reference only

Electrical Characteristics (Ta=25degC) (*1)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Reverse stand-off voltage	V _{RWM}	-	-	5.0	V	
Leakage current	I _R	-	-	1.0	uA	V _{RWM} = 5.0V
Breakdown voltage	V _{BR}	6.5	7.7	8.8	V	I _R = 1mA
Clamping voltage	V _{c1}	-	-	10.5	V	I _{pp} =1A , tp=8/20us
	V _{c2}	-	-	14.0	V	I _{pp} =3A , tp=8/20us
Capacitance	C	-	0.5	0.9	pF	V _R = 0V, f = 1MHz

*1 All values for reference on a SOT-23 package configuration
(front: Au wire 20um, back: Au eutectic)

Note

1. Assembly

Example: DFN0603

